

## **Dual N-Channel 20-V (D-S) MOSFET**

PRODUCT SUMMARY									
V <sub>DS</sub> (V)	$R_{DS(on)}\left(\Omega\right)$	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)						
20	0.046 at V <sub>GS</sub> = 4.5 V	4.5	3.5 nC						
	$0.063$ at $V_{GS} = 2.5 \text{ V}$	4.5	3.5 110						

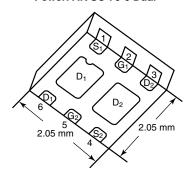
#### **FEATURES**

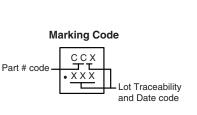
- Halogen-free According to IEC 61249-2-21
- TrenchFET<sup>®</sup> Power MOSFET
- New Thermally Enhanced PowerPAK<sup>®</sup> SC-70 Package
  - Small Footprint Area
  - Low On-Resistance
- Typical ESD Protection 560 V

## Pb-free

ROHS COMPLIANT HALOGEN FREE

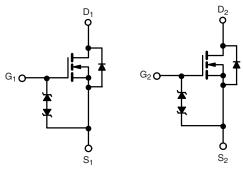
#### PowerPAK SC-70-6 Dual





## **APPLICATIONS**

- Load Switch for Portable Applications
- High Frequency DC/DC Converter



Ordering Information: SiA906EDJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

N-Channel MOSFET

N-Channel MOSFET

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		$V_{DS}$	20	V	
Gate-Source Voltage		V <sub>GS</sub>	± 12	v	
	T <sub>C</sub> = 25 °C		4.5 <sup>a</sup>		
Continuous Drain Current (T <sub>.1</sub> = 150 °C)	T <sub>C</sub> = 70 °C	I <sub>D</sub>	4.5 <sup>a</sup>		
Continuous Diam Current (1) = 130 °C)	T <sub>A</sub> = 25 °C	יט [	4.5 <sup>a, b, c</sup>		
	T <sub>A</sub> = 70 °C		4.1 <sup>b, c</sup>	A	
Pulsed Drain Current		I <sub>DM</sub>	15		
Continuous Source-Drain Diode Current	T <sub>C</sub> = 25 °C		4.5 <sup>a</sup>		
Continuous Source-Drain Diode Current	T <sub>A</sub> = 25 °C	I <sub>S</sub>	1.6 <sup>b, c</sup>		
	T <sub>C</sub> = 25 °C		7.8		
Maximum Power Dissipation	T <sub>C</sub> = 70 °C	P <sub>D</sub>	5	w	
Maximum Fower Dissipation	T <sub>A</sub> = 25 °C	] 'U	1.9 <sup>b, c</sup>	VV	
	T <sub>A</sub> = 70 °C		1.2 <sup>b, c</sup>		
Operating Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C		
Soldering Recommendations (Peak Tempera	ature) <sup>d, e</sup>		260		

THERMAL RESISTANCE RATINGS										
Parameter		Symbol	Typical	Maximum	Unit					
Maximum Junction-to-Ambient <sup>b, f</sup>	t ≤ 5 s	$R_{thJA}$	52	65	°C/W					
Maximum Junction-to-Case (Drain)	Steady State	R <sub>th IC</sub>	12.5	16	] 5/ ٧٧					

#### Notes:

- a. Package limited
- b. Surface Mounted on 1" x 1" FR4 board.
- c. t = 5 s.
- d. See Solder Profile (<a href="www.vishay.com/ppg?73257">www.vishay.com/ppg?73257</a>). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under Steady State conditions is 110 °C/W.

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static	,			, ,,	l	1
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	20			V
V <sub>DS</sub> Temperature Coefficient	$\Delta V_{DS}/T_{J}$	J 050 A		23		mV/°C
V <sub>GS(th)</sub> Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I <sub>D</sub> = 250 μA		- 3.3		
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_{D} = 250 \mu A$	0.6		1.4	V
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			± 8	
		$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}$			- 1	μΑ
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C			- 10	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \le 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	10			Α
_		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 3.9 A		0.037	0.046	_
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 2.5 V, I <sub>D</sub> = 3.3 A		0.051	0.063	Ω
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 3.9 A		14		S
Dynamic <sup>b</sup>						
Input Capacitance	C <sub>iss</sub>			350		
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz		63		pF
Reverse Transfer Capacitance	C <sub>rss</sub>			37		1
·	.00	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 5.1 A		7.5	12	nC
Total Gate Charge	$Q_g$			3.5	5.5	
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 5.1 \text{ A}$		0.95		
Gate-Drain Charge	$Q_{gd}$			0.75		
Gate Resistance	$R_{g}$	f = 1 MHz		3.5		Ω
Turn-on Delay Time	t <sub>d(on)</sub>			10	15	
Rise Time	t <sub>r</sub>	V 40V B 04.0		12	20	- ns
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{DD}$ = 10 V, $R_L$ = 2.4 $\Omega$ $I_D \cong 4.1$ A, $V_{GEN}$ = 4.5 V, $R_q$ = 1 $\Omega$		18	30	
Fall Time	t <sub>f</sub>	ID = 4.1  A,  VGEN - 4.3  V,  Hg - 1.52		12	20	
Turn-on Delay Time	t <sub>d(on)</sub>			5	10	
Rise Time	t <sub>r</sub>	V 40V D 040		12	20	
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{DD}$ = 10 V, R <sub>L</sub> = 2.4 Ω $I_{D} \cong 4.1$ A, $V_{GEN}$ = 10 V, R <sub>q</sub> = 1 Ω		15	25	
Fall Time	t <sub>f</sub>	ID = 4.1  A,  VGEN - 10  V,  Hg - 122		10	15	
Drain-Source Body Diode Characteristic	s			l.		
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C			4.5	۸
Pulse Diode Forward Current	I <sub>SM</sub>				15	A
Body Diode Voltage	$V_{SD}$	I <sub>S</sub> = 4.1 A, V <sub>GS</sub> = 0 V		0.8	1.2	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>			15	30	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	L = 4.1 A dl/dt = 100 A/··· T		8	20	nC
Reverse Recovery Fall Time	t <sub>a</sub>	$I_F = 4.1 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^{\circ}\text{C}$		8		
Reverse Recovery Rise Time	t <sub>b</sub>			7		ns

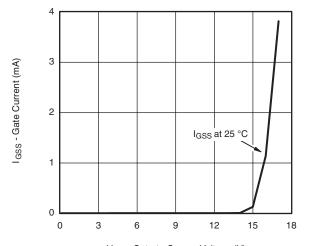
#### Notes:

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

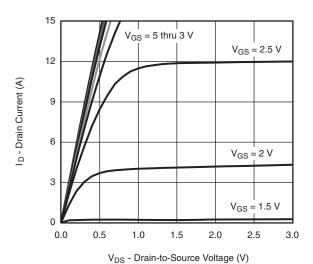


## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

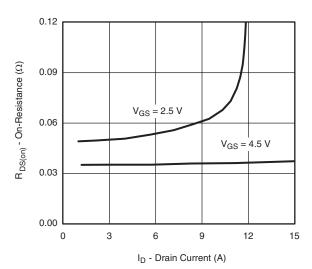


V<sub>GS</sub> - Gate-to-Source Voltage (V)

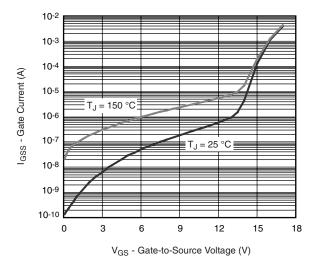
#### Gate Current vs. Gate-Source Voltage



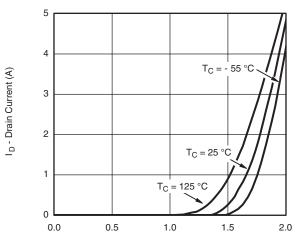
**Output Characteristics** 



On-Resistance vs. Drain Current and Gate Voltage

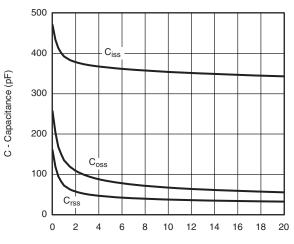


Gate Current vs. Gate-Source Voltage



 $V_{GS}$  - Gate-to-Source Voltage (V)

#### **Transfer Characteristics**



V<sub>DS</sub> - Drain-to-Source Voltage (V)

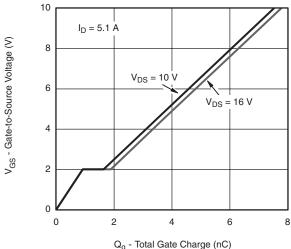
Capacitance

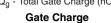
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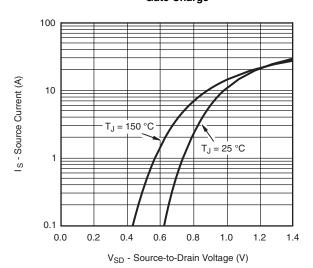
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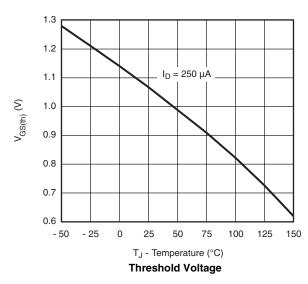
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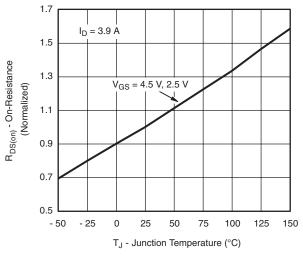




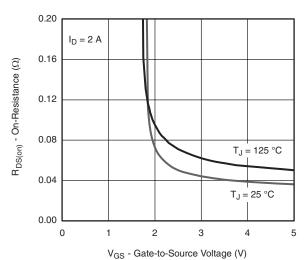


Source-Drain Diode Forward Voltage

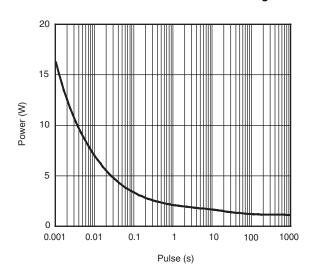




On-Resistance vs. Junction Temperature



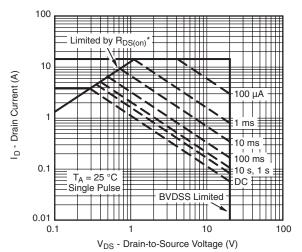
On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power (Junction-to-Ambient)



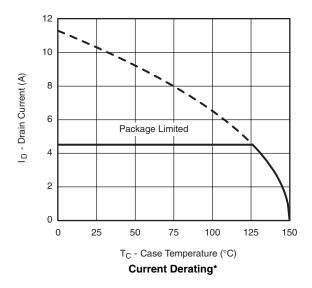
#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

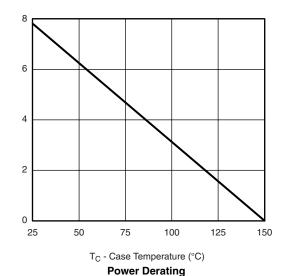


\*  $V_{GS} > \mbox{ minimum } V_{GS}$  at which  $R_{DS(on)}$  is specified

#### Safe Operating Area, Junction-to-Ambient

Power Dissipation (W)





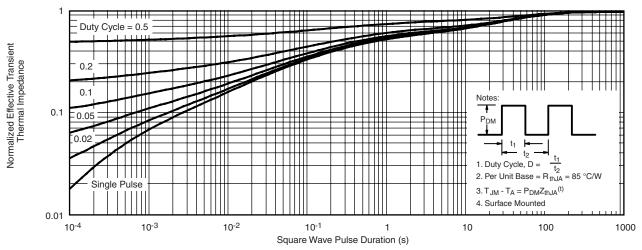
<sup>\*</sup> The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

## SiA906EDJ

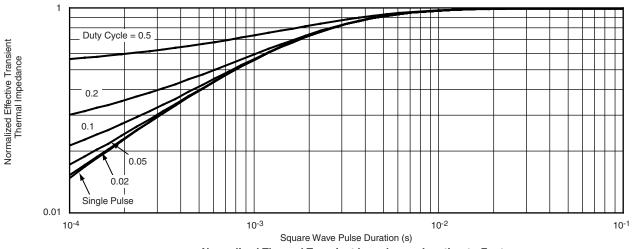
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#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



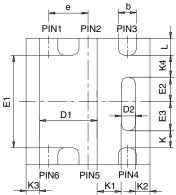
Normalized Thermal Transient Impedance, Junction-to-Foot

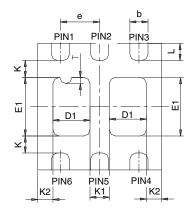
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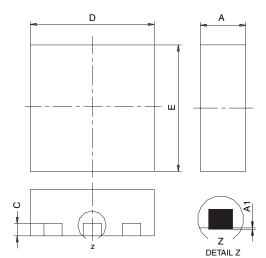
## PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
  Package outline exclusive of mold flash and metal burr
  Package outline inclusive of plating

			SINGL	E PAD		DUAL PAD						
DIM	M	ILLIMETER	RS		INCHES		M	ILLIMETER	RS		INCHES	
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028
D2	0.135	0.235	0.335	0.005	0.009	0.013						
Е	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041
E2	0.345	0.395	0.445	0.014	0.016	0.018						
E3	0.425	0.475	0.525	0.017	0.019	0.021						
е		0.65 BSC			0.026 BSC	,	0.65 BSC			0.026 BSC		
K		0.275 TYP	1		0.011 TYP		0.275 TYP			0.011 TYP		
K1		0.400 TYP	1	0.016 TYP			0.320 TYP			0.013 TYP		
K2		0.240 TYP	1	0.009 TYP			0.252 TYP			0.010 TYP		
К3		0.225 TYP	1	0.009 TYP								
K4		0.355 TYP	1	0.014 TYP								
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015
Т							0.05	0.10	0.15	0.002	0.004	0.006
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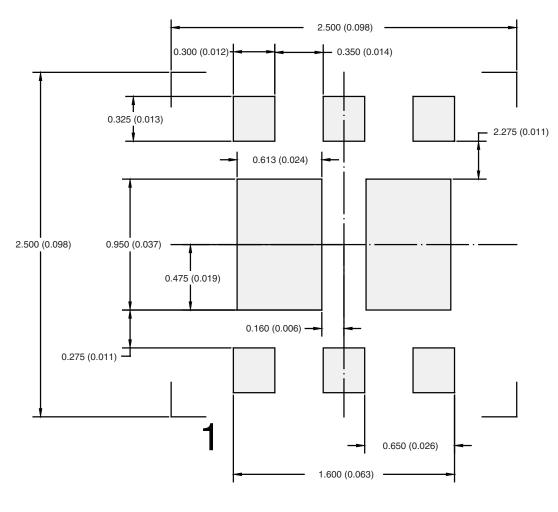
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DWG: 5934

Document Number: 73001 06-Aug-07



### RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Dual



Dimensions in mm/(Inches)

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